



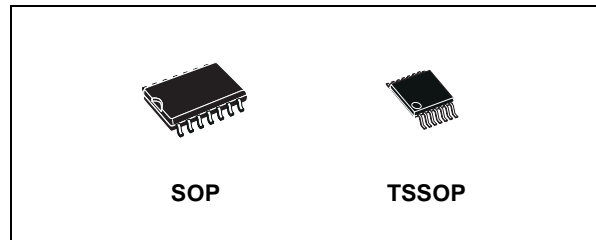
74VHCT32A

QUAD 2-INPUT OR GATE

- HIGH SPEED: $t_{PD} = 5 \text{ ns}$ (TYP.) at $V_{CC} = 5V$
- LOW POWER DISSIPATION:
 $I_{CC} = 2 \mu\text{A}$ (MAX.) at $T_A = 25^\circ\text{C}$
- COMPATIBLE WITH TTL OUTPUTS:
 $V_{IH} = 2V$ (MIN.), $V_{IL} = 0.8V$ (MAX)
- POWER DOWN PROTECTION ON INPUTS & OUTPUTS
- SYMMETRICAL OUTPUT IMPEDANCE:
 $|I_{OH}| = I_{OL} = 8 \text{ mA}$ (MIN)
- BALANCED PROPAGATION DELAYS:
 $t_{PLH} \approx t_{PHL}$
- OPERATING VOLTAGE RANGE:
 $V_{CC}(\text{OPR}) = 4.5V$ to $5.5V$
- PIN AND FUNCTION COMPATIBLE WITH 74 SERIES 32
- IMPROVED LATCH-UP IMMUNITY
- LOW NOISE: $V_{OLP} = 0.8V$ (MAX.)

DESCRIPTION

The 74VHCT32A is an advanced high-speed CMOS QUAD 2-INPUT OR GATE fabricated with sub-micron silicon gate and double-layer metal wiring C²MOS technology. The internal circuit is composed of 3 stages including buffer output, which provides high noise immunity and stable output.

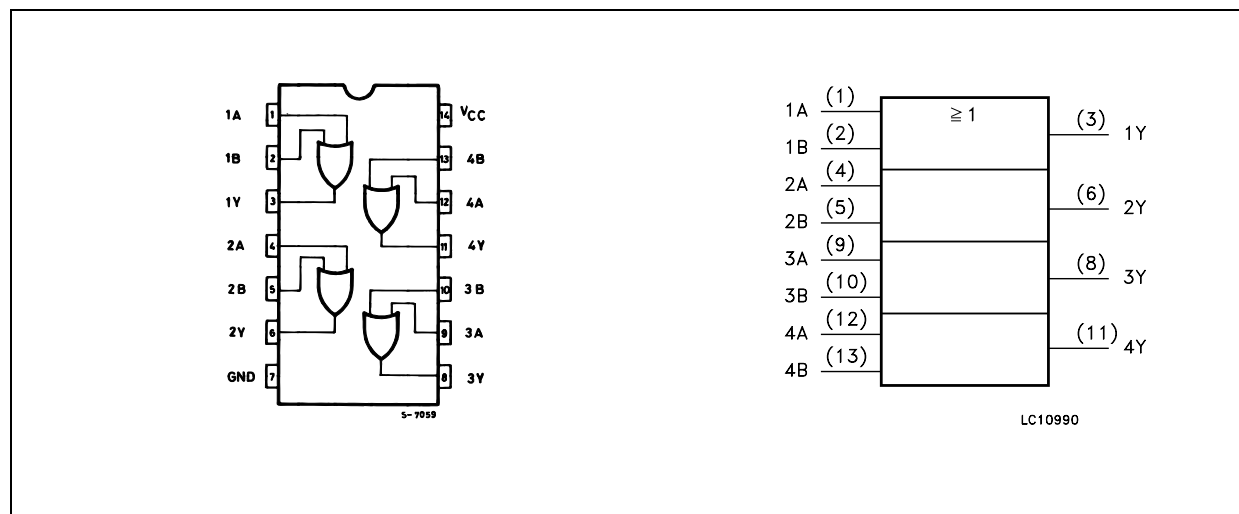


ORDER CODES

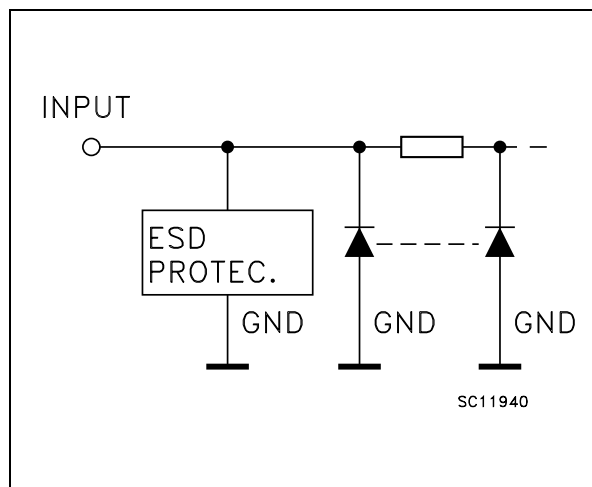
PACKAGE	TUBE	T & R
SOP	74VHCT32AM	74VHCT32AMTR
TSSOP		74VHCT32ATTR

Power down protection is provided on all inputs and outputs and 0 to 7V can be accepted on inputs with no regard to the supply voltage. This device can be used to interface 5V to 3V since all inputs are equipped with TTL threshold. All inputs and outputs are equipped with protection circuits against static discharge, giving them 2KV ESD immunity and transient excess voltage.

PIN CONNECTION AND IEC LOGIC SYMBOLS



INPUT EQUIVALENT CIRCUIT



PIN DESCRIPTION

PIN No	SYMBOL	NAME AND FUNCTION
1, 4, 9, 12	1A to 4A	Data Inputs
2, 5, 10, 13	1B to 4B	Data Inputs
3, 6, 8, 11	1Y to 4Y	Data Outputs
7	GND	Ground (0V)
14	V_{CC}	Positive Supply Voltage

TRUTH TABLE

A	B	Y
L	L	L
L	H	H
H	L	H
H	H	H

ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
V_{CC}	Supply Voltage	-0.5 to +7.0	V
V_I	DC Input Voltage	-0.5 to +7.0	V
V_O	DC Output Voltage (see note 1)	-0.5 to +7.0	V
V_O	DC Output Voltage (see note 2)	-0.5 to $V_{CC} + 0.5$	V
I_{IK}	DC Input Diode Current	- 20	mA
I_{OK}	DC Output Diode Current	± 20	mA
I_O	DC Output Current	± 25	mA
I_{CC} or I_{GND}	DC V_{CC} or Ground Current	± 50	mA
T_{stg}	Storage Temperature	-65 to +150	$^{\circ}C$
T_L	Lead Temperature (10 sec)	300	$^{\circ}C$

Absolute Maximum Ratings are those values beyond which damage to the device may occur. Functional operation under these conditions is not implied
 1) $V_{CC} = 0V$
 2) High or Low State

RECOMMENDED OPERATING CONDITIONS

Symbol	Parameter	Value	Unit
V_{CC}	Supply Voltage	4.5 to 5.5	V
V_I	Input Voltage	0 to 5.5	V
V_O	Output Voltage (see note 1)	0 to 5.5	V
V_O	Output Voltage (see note 2)	0 to V_{CC}	V
T_{op}	Operating Temperature	-55 to 125	$^{\circ}C$
dt/dv	Input Rise and Fall Time (see note 3) ($V_{CC} = 5.0 \pm 0.5V$)	0 to 20	ns/V

1) $V_{CC} = 0V$
 2) High or Low State
 3) V_{IN} from 0.8V to 2V

DC SPECIFICATIONS

Symbol	Parameter	Test Condition		Value						Unit	
		V _{CC} (V)		T _A = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.
V _{IH}	High Level Input Voltage	4.5 to 5.5		2			2		2		V
V _{IL}	Low Level Input Voltage	4.5 to 5.5				0.8		0.8		0.8	V
V _{OH}	High Level Output Voltage	4.5	I _O =-50 μA	4.4	4.5		4.4		4.4		V
		4.5	I _O =-8 mA	3.94			3.8		3.7		
V _{OL}	Low Level Output Voltage	4.5	I _O =50 μA		0.0	0.1		0.1		0.1	V
		4.5	I _O =8 mA			0.36		0.44		0.55	
I _I	Input Leakage Current	0 to 5.5	V _I = 5.5V or GND			± 0.1		± 1.0		± 1.0	μA
I _{CC}	Quiescent Supply Current	5.5	V _I = V _{CC} or GND			2		20		20	μA
Δ I _{CC}	Additional Worst Case Supply Current	5.5	One Input at 3.4V, other input at V _{CC} or GND			1.35		1.5		1.5	mA
I _{OPD}	Output Leakage Current	0	V _{OUT} = 5.5V			0.5		5.0		5.0	μA

AC ELECTRICAL CHARACTERISTICS (Input t_r = t_f = 3ns)

Symbol	Parameter	Test Condition		Value						Unit	
		V _{CC} (*) (V)	C _L (pF)	T _A = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.
t _{PLH} t _{PHL}	Propagation Delay Time	5.0	15		5.0	7.0	1.0	8.0	1.0	8.0	ns
		5.0	50		5.5	8.0	1.0	9.0	1.0	9.0	

(*) Voltage range is 5.0V ± 0.5V

CAPACITIVE CHARACTERISTICS

Symbol	Parameter	Test Condition		Value						Unit	
				T _A = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.
C _{IN}	Input Capacitance				4	10		10		10	pF
C _{PD}	Power Dissipation Capacitance (note 1)				18						pF

1) C_{PD} is defined as the value of the IC's internal equivalent capacitance which is calculated from the operating current consumption without load. (Refer to Test Circuit). Average operating current can be obtained by the following equation. I_{CC(opr)} = C_{PD} × V_{CC} × f_{IN} + I_{CC}/4 (per gate)

DYNAMIC SWITCHING CHARACTERISTICS

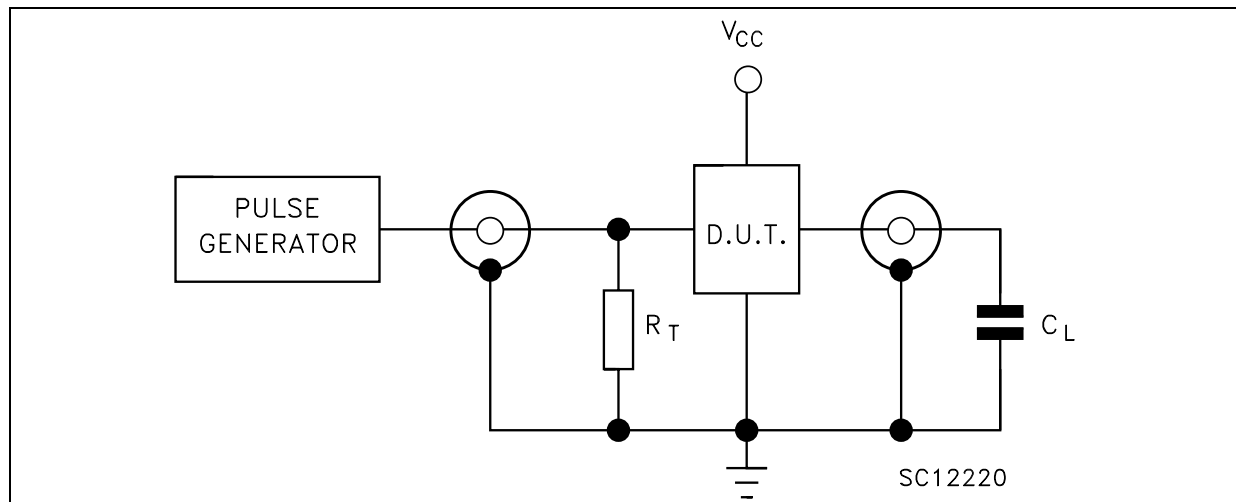
Symbol	Parameter	Test Condition		Value						Unit	
		V _{CC} (V)	C _L = 50 pF	T _A = 25°C			-40 to 85°C		-55 to 125°C		
				Min.	Typ.	Max.	Min.	Max.	Min.		Max.
V _{OLP}	Dynamic Low Voltage Quiet Output (note 1, 2)	5.0	C _L = 50 pF		0.3	0.8					V
V _{OLV}				-0.8	-0.3						
V _{IHD}	Dynamic High Voltage Input (note 1, 3)	5.0		2.0							
V _{ILD}	Dynamic Low Voltage Input (note 1, 3)	5.0				0.8					

1) Worst case package.

2) Max number of outputs defined as (n). Data inputs are driven 0V to 3.0V, (n-1) outputs switching and one output at GND.

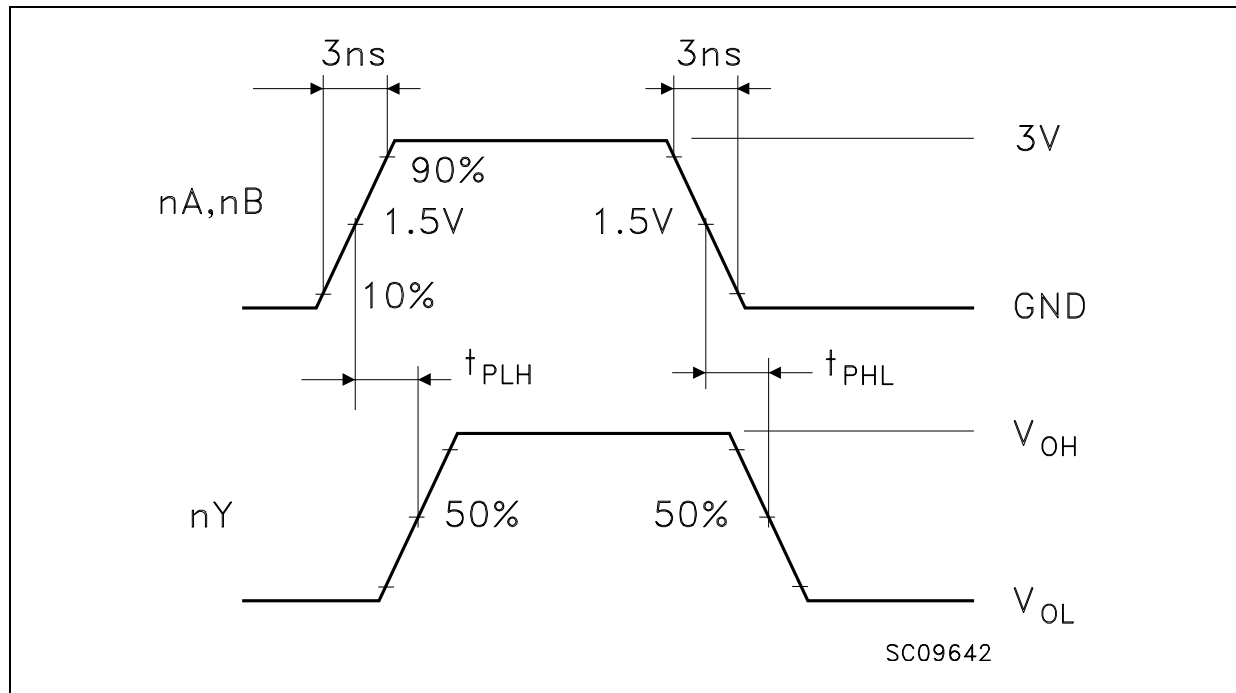
3) Max number of data inputs (n) switching. (n-1) switching 0V to 3.0V. Inputs under test switching: 3.0V to threshold (V_{ILD}), 0V to threshold (V_{IHD}), f=1MHz.

TEST CIRCUIT



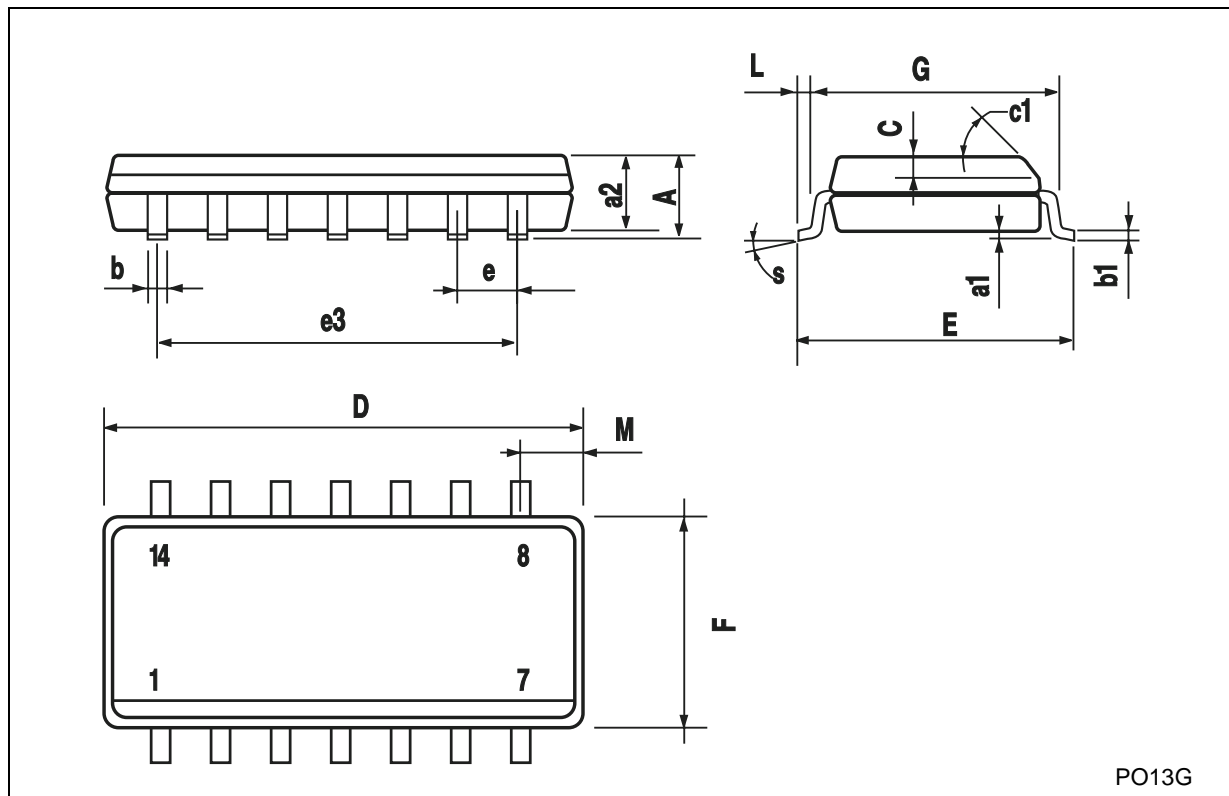
C_L = 15/50pF or equivalent (includes jig and probe capacitance)

R_T = Z_{OUT} of pulse generator (typically 50Ω)

WAVEFORM: PROPAGATION DELAYS (f=1MHz; 50% duty cycle)

SO-14 MECHANICAL DATA

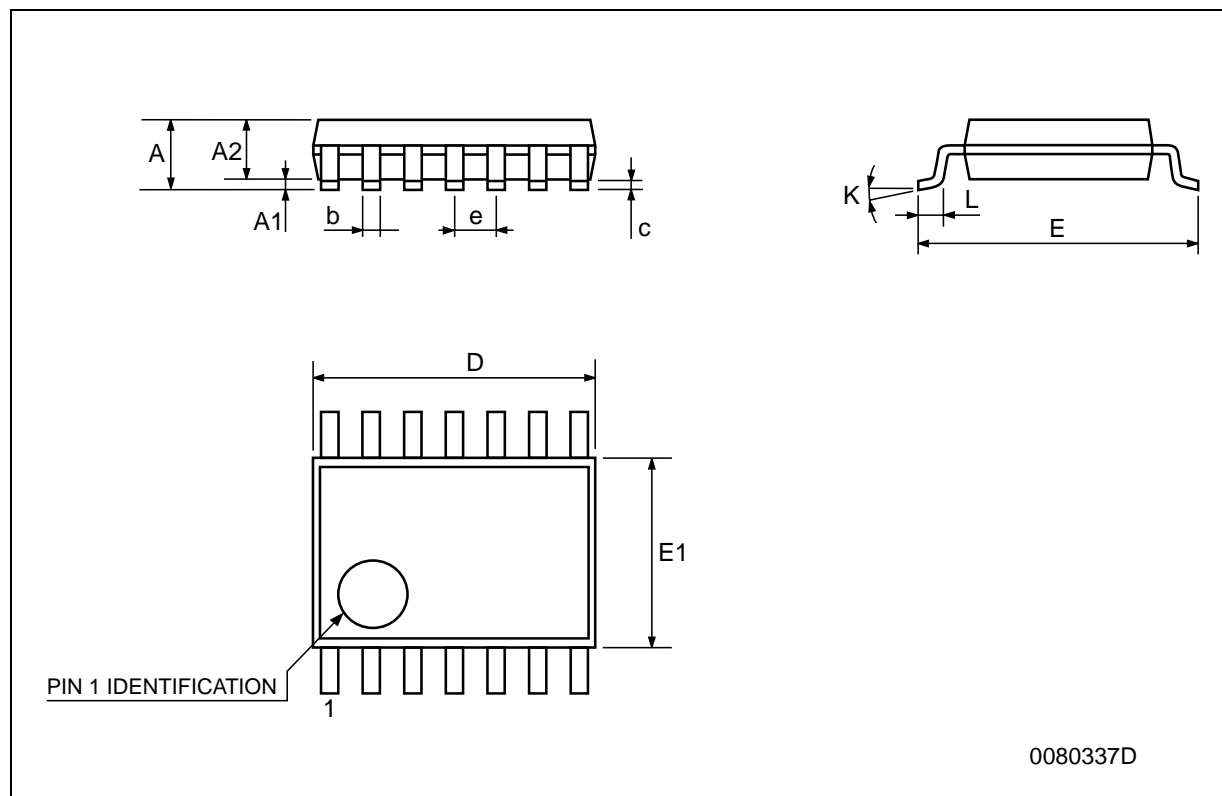
DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.75			0.068
a1	0.1		0.2	0.003		0.007
a2			1.65			0.064
b	0.35		0.46	0.013		0.018
b1	0.19		0.25	0.007		0.010
C		0.5			0.019	
c1	45° (typ.)					
D	8.55		8.75	0.336		0.344
E	5.8		6.2	0.228		0.244
e		1.27			0.050	
e3		7.62			0.300	
F	3.8		4.0	0.149		0.157
G	4.6		5.3	0.181		0.208
L	0.5		1.27	0.019		0.050
M			0.68			0.026
S	8° (max.)					



PO13G

TSSOP14 MECHANICAL DATA

DIM.	mm.			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A			1.2			0.047
A1	0.05		0.15	0.002	0.004	0.006
A2	0.8	1	1.05	0.031	0.039	0.041
b	0.19		0.30	0.007		0.012
c	0.09		0.20	0.004		0.0089
D	4.9	5	5.1	0.193	0.197	0.201
E	6.2	6.4	6.6	0.244	0.252	0.260
E1	4.3	4.4	4.48	0.169	0.173	0.176
e		0.65 BSC			0.0256 BSC	
K	0°		8°	0°		8°
L	0.45	0.60	0.75	0.018	0.024	0.030



Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specifications mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

© The ST logo is a registered trademark of STMicroelectronics

© 2001 STMicroelectronics - Printed in Italy - All Rights Reserved
STMicroelectronics GROUP OF COMPANIES

Australia - Brazil - China - Finland - France - Germany - Hong Kong - India - Italy - Japan - Malaysia - Malta - Morocco
Singapore - Spain - Sweden - Switzerland - United Kingdom

© <http://www.st.com>